



Attorney's Docket No.: 42P16680

Patent

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:)		
)		
Justin K. Brask et al.)	Examiner:	Fenty, Jesse A.
)		
U.S. Serial No:)	Art Unit:	2815
10/750,061)		
)		
Filed:)		
December 30, 2003)		
)		
For: NONPLANAR TRANSISTOR WITH)		
METAL GATE ELECTRODES)		
)		

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

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Enclosed is a copy of Information Disclosure Citation Form PTO-1449 or PTO/SB/08 together with copies of the documents cited on that form, except for copies not required to be submitted (e.g., copies of U.S. patents and U.S. published patent applications need not be enclosed). It is respectfully requested that the cited documents be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449 or PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

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Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Dated: 12/27, 2004

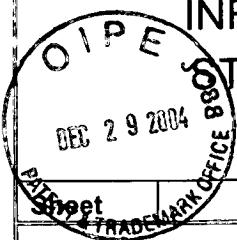

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INFORMATION DISCLOSURE

STATEMENT BY APPLICANT

(use as many sheets as necessary)



Complete if Known

Application Number	10/750,061
Filing Date	December 30, 2003
First Named Inventor:	Justin K. Brask et al.
Art Unit	2815
Examiner Name	Fenty, Jesse A.
Attorney Docket Number	42P16680

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U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (If known)				
		US-	6,716,684 B1	4/6/2004	Krivokapic et al.	
		US-	6,680,240 B1	1/20/2004	Maszara	
		US-	6,562,665 B1	5/13/2003	Yu	
		US-	6,525,403 B2	2/25/2003	Inaba et al.	
		US-	6,475,869 B1	11/5/2002	Yu	
		US-	5,563,077	10/8/1996	Ha	
		US-	5,346,839	9/13/1994	Sundaresan	
		US-	2002/0081794 A1	6/27/2002	Ito	
		US-	2002/0167007 A1	11/14/2002	Yamazaki et al.	
		US-	6,483,156 B1	11/19/2002	Adkisson et al.	
		US-	5,578,513	11/26/1996	Maegawa	
		US-	6,413,802 B1	7/2/2002	Hu et al.	
		US-	6,730,964 B2	5/4/2004	Horiuchi	
		US-	5,716,879	2/10/1998	Choi et al.	
		US-	6,611,029 B1	8/26/2003	Ahmed et al.	
			5,658,806	8/19/1997	Lin et al.	
			6,376,317 B1	4/23/2002	Forbes et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
		EP 0 623 963 A1	11/9/1994	Siemens AG		
		WO 02/43151A	5/30/2002	Hitachi ULSI Sys Co Ltd		

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹Applicant's unique citation designation number (optional). ²See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SENT FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450.

Substitute for Form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			Complete if Known		
			Application Number	10/750,061	
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			First Named Inventor:	Justin K. Brask et al.	
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			Examiner Name	Fenty, Jesse A.	
Sheet	2	of	2	Attorney Docket Number	42P16680
NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T ²
		V. Subramanian et al., "A Bulk-Si-Compatible Ultrathin-body SOI Technology for Sub-100m MOSFETS" Proceeding of the 57th Annual Device Research Conference, pp. 28-29 (1999)			
		Hisamoto et al., "A Folded-channel MOSFET for Deepsub-tenth Micron Era", 1998 IEEE International Electron Device Meeting Technical Digest, pp 1032-1034 (1998)			
		Huang et al., "Sub 50-nm FinFET: PMOS", 1999 IEEE International Electron Device Meeting Technical Digest, pp 67-70 (1999)			
		Auth et al., "Vertical, Fully-Depleted, Surroundings Gate MOSFETS On sub-0.1um Thick Silicon Pillars", 1996 54th Annual Device Research Conference Digest, pp 108-109 (1996)			
		Hisamoto et al., "A Fully Depleted Lean-Channel Transistor (DELTA)-A Novel Vertical Ultrathin SOI MOSFET", IEEE Electron Device Letters, V. 11(1), pp36-38 (1990).			
		Jong-Tae Park et al., "Pi-Gate SOI MOSFET" IEEE Electron Device Letters, Vol. 22, No. 8, August 2001, pages 405-406			
		Hisamoto, Digh et al. "FinFET- A Self-Aligned Double-Gate MOSFET Scalable to 20 nm", IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325			
		International Search Report PCT/US 03/26242			
		International Search Report PCT/US 03/39727			
		International Search Report PCT/US 03/40320			